

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	15	Kang-Sung-Taeg.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:12
L2	2	("5559735"   "5780893").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 17:22
L3	2	("5559735"   "5780893").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 17:27
L4	11	("5559735").URPN.	USPAT	OR	ON	2005/04/26 17:36
L5	1843	(non\$1volatile with memory) and gate and source and drain and spacer	USPAT	OR	ON	2005/04/26 17:37
L6	1336	5 and (gate same (mask or masking))	USPAT	OR	ON	2005/04/26 17:37
L7	1276	6 and (polysilicon or (poly\$1crystalline adj silicon))	USPAT	OR	ON	2005/04/26 17:37
L8	3170	(non\$1volatile with memory) and gate and source and drain and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:38
L9	1940	8 and ((mask or masking) with (gate or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:38
L10	1446	9 and @ay<="2002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:39
L11	1156	10 and ((doping or dopant or doped or implant\$3) with (source or drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:40

L12	820	11 and tunnel\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:40
L13	791	12 and (polysilicon or (poly\$1crystalline adj silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:41
L14	527	13 and (stack or stacking or stacked)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:42
L15	511	14 and (etch or etching)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:43
L16	490	15 and (non\$1volatile near3 memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:43
L17	64	16 and (charge\$1 near3 trap\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:47
L18	2	"6734107".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:49
L19	2	"6657893".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:49

L20	3791	438/694.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:50
L21	459	438/696.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:50
L22	3027	438/706.ccls. 438/719.ccls. 438/723.ccls. 438/724.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:50
L23	7035	20 or 21 or 22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:50
L24	423	23 and gate and spacer and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:51
L25	380	24 and @ay<="2002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:51
L26	321	25 and (mask or masking)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:51
L27	33	26 and tunnel\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 17:51
S1	4228	memory and ((polysilicon or (poly\$1crystalline adj silicon)) with spacer)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/26 17:11

S2	4145	S1 and (gate or electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:07
S3	3539	S2 and (source and drain)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:07
S4	3380	S3 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:08
S5	812	S4 and tunneling	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:08
S6	555	S5 and non\$1volatile	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:11
S7	440	S6 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S8	420	S7 and (mask or resist or photo\$1resist or photo\$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S9	420	S8 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S10	387	S8 and (dope or doping or dopant or implant\$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S11	368	S10 and (non\$1volatile near3 memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:11